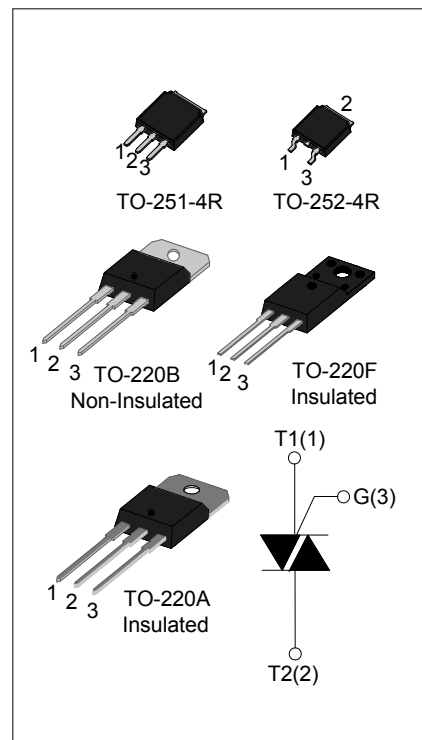




DESCRIPTION:

With high ability to withstand the shock loading of large current, JST06 series triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, the products especially recommended for use on inductive load.

From all three terminals to external heatsink, JST06A provides a rated insulation voltage of 2500 V_{RMS}, and JST06F provides a rated insulation voltage of 2000 V_{RMS}, complying with UL standards (File ref: E252906).



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	6	A
V_{DRM}/V_{RRM}	600 and 800	V

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40 - 150	°C
Operating junction temperature range	T_j	-40 - 125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600/800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600/800	V
Non repetitive surge peak Off-state voltage	V_{DSM}	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage	V_{RSM}	$V_{RRM} + 100$	V
RMS on-state current	TO-251-4R/ TO-252-4R/ TO-220B(Non-Ins) ($T_C=107^\circ\text{C}$)	6	A
	TO-220A(Ins) ($T_C=100^\circ\text{C}$)		
	TO-220F(Ins) ($T_C=97^\circ\text{C}$)		

Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	60	A
I^2t value for fusing ($t_p=10ms$)	I^2t	18	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	di/dt	50	$A/\mu s$
Peak gate current	I_{GM}	2	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value				Unit
				TW	SW	CW	BW	
I_{GT}	$V_D=12V R_L=30\Omega$	I - II -III	MAX	5	10	35	50	mA
V_{GT}		I - II -III	MAX	1.5				V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ C$ $R_L=3.3K\Omega$	I - II -III	MIN	0.2				V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	10	15	50	70	mA
		II		15	25	60	80	
I_H	$I_{TM}=0.2A$		MAX	6	10	35	60	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ C$		MIN	50	100	400	1000	$V/\mu s$

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=8.5A t_p=380\mu s$	$T_j=25^\circ C$	1.5	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ C$	5	μA
I_{RRM}		$T_j=125^\circ C$	1	mA

THERMAL RESISTANCES

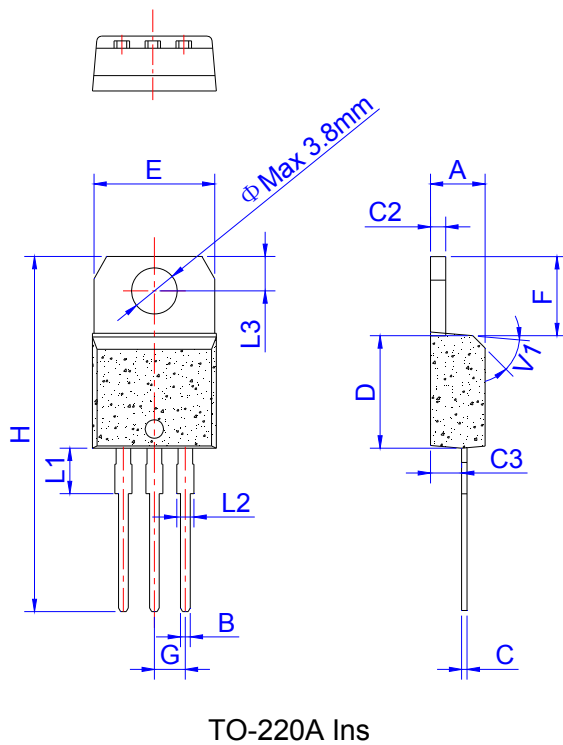
Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-251-4R/ TO-252-4R	2.7	$^\circ C/W$
		TO-220A(Ins)	3.3	

$R_{th(j-c)}$	junction to case(AC)	TO-220F(Ins)	3.1	°C/W
		TO-220B(Non-Ins)	2.2	

ORDERING INFORMATION

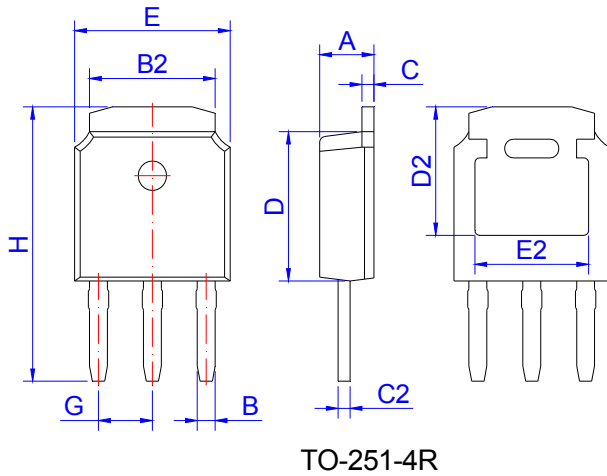
J	ST	06	B	-600	TW
JieJie Microelectronics Co.,Ltd	Triacs	$I_{T(RMS)}:6A$			TW: $I_{GT1-3} \leq 5mA$ SW: $I_{GT1-3} \leq 10mA$ CW: $I_{GT1-3} \leq 35mA$ BW: $I_{GT1-3} \leq 50mA$
		B:TO-220B(Non-Ins) H:TO-251-4R K:TO-252-4R A:TO-220A(Ins) F:TO-220F(Ins)		600: $V_{DRM} / V_{RRM} \geq 600V$ 800: $V_{DRM} / V_{RRM} \geq 800V$	

PACKAGE MECHANICAL DATA

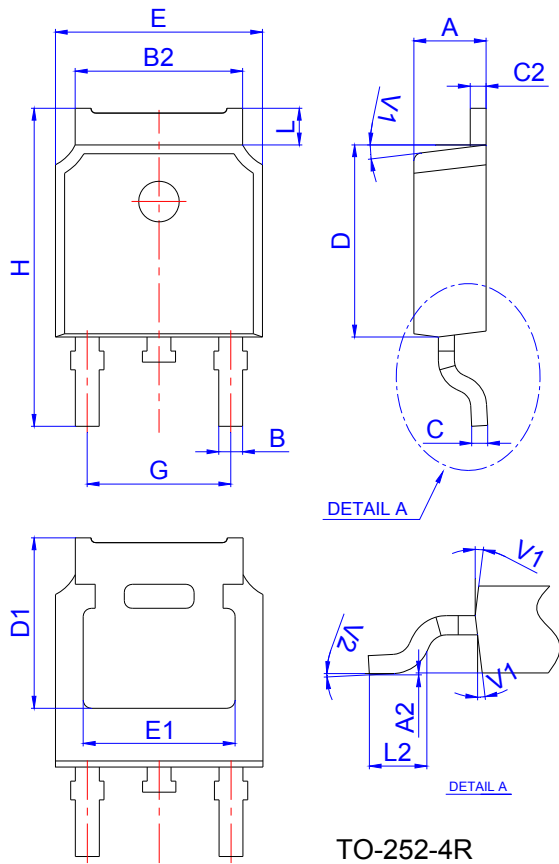


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

PACKAGE MECHANICAL DATA

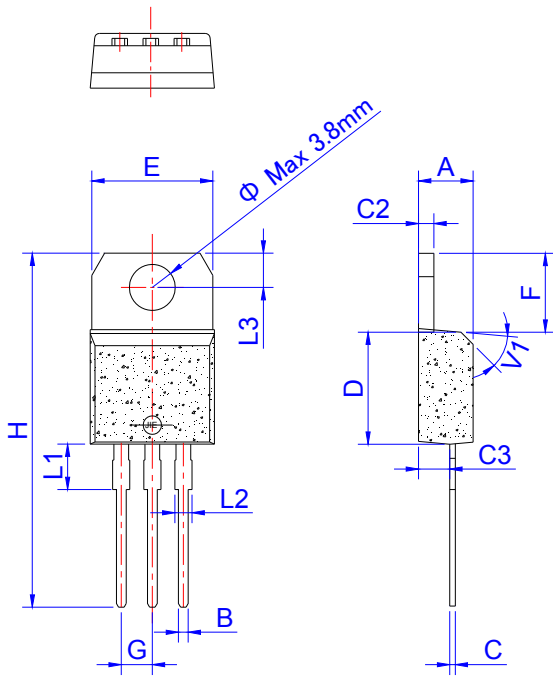


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10	2.30	2.50	0.083	0.091	0.098
B	0.66	0.76	0.86	0.026	0.030	0.034
B2	5.15	5.33	5.48	0.203	0.210	0.216
C	0.44	0.51	0.58	0.017	0.020	0.023
C2	0.44	0.51	0.58	0.017	0.020	0.023
D	5.90	6.10	6.30	0.232	0.240	0.248
D2	5.30 REF			0.209 REF		
E	6.40	6.60	6.80	0.252	0.260	0.268
E2	4.83 REF			0.190 REF		
G	2.19	2.29	2.39	0.086	0.090	0.094
H	10.60	11.20	11.80	0.417	0.441	0.465



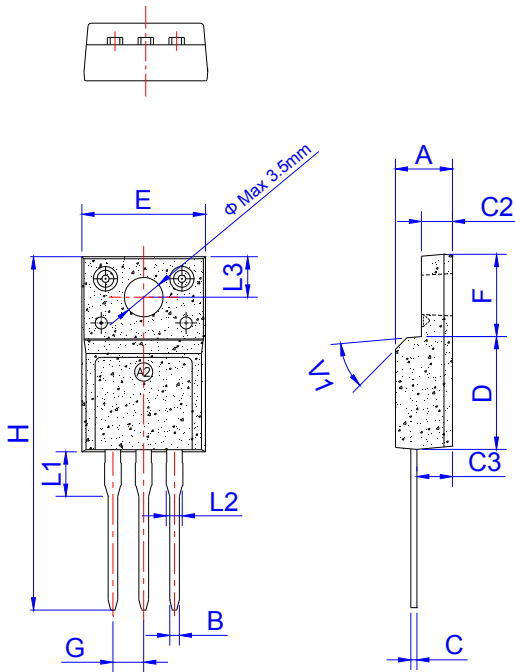
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

PACKAGE MECHANICAL DATA



TO-220B Non-Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



TO-220F Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

FIG.1: Maximum power dissipation versus RMS on-state current

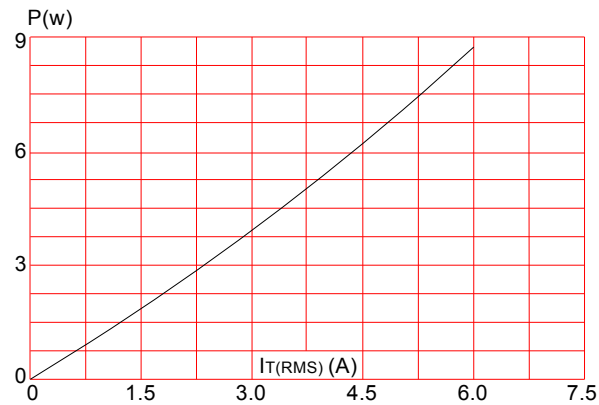


FIG.3: Surge peak on-state current versus number of cycles

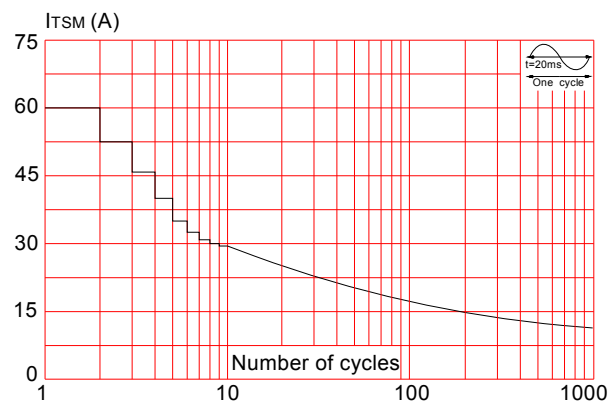


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

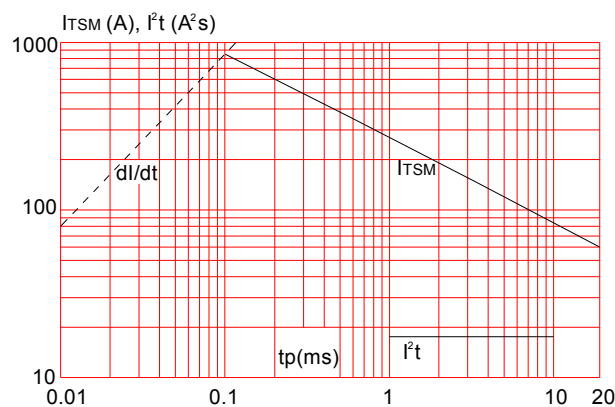


FIG.2: RMS on-state current versus case temperature

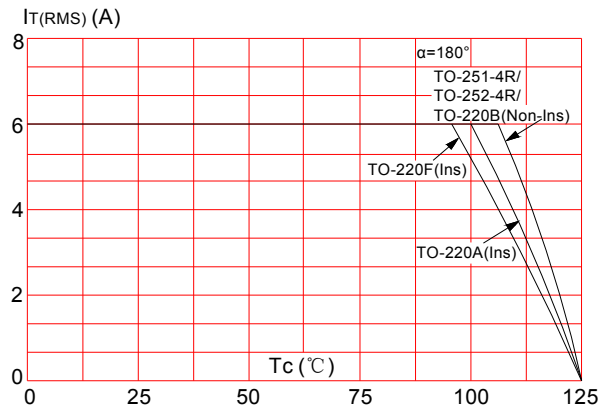


FIG.4: On-state characteristics (maximum values)

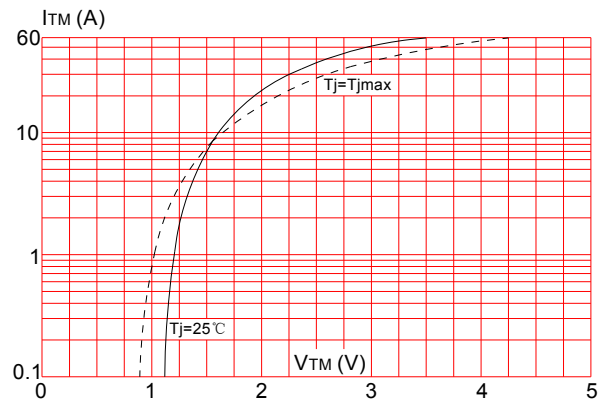
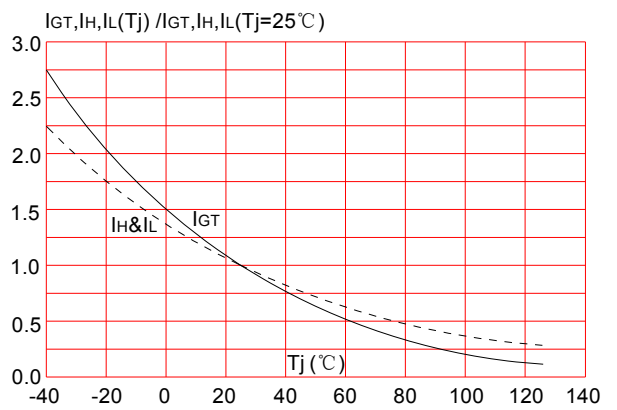


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature




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